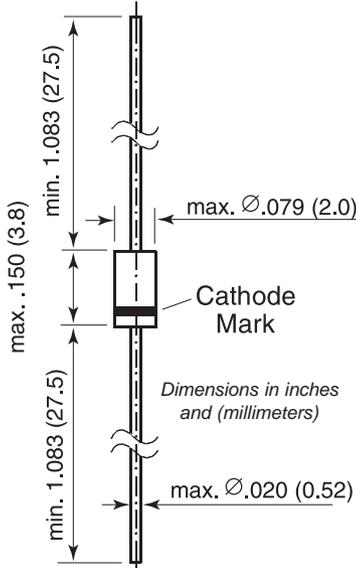




Small-Signal Diode

Reverse Voltage 100V
Forward Current 150mA

DO-204AH (DO-35 Glass)



Features

- Silicon Epitaxial Planar Diode
- Fast switching diode

Mechanical Data

Case: DO-35 Glass Case

Weight: approx. 0.13g

Packaging Codes/Options:

F2/10K per Ammo tape (52mm), 50K/box
F3/10K per 13" reel (52mm tape), 50K/box

Maximum Ratings and Thermal Characteristics (T_A = 25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Reverse voltage	V _R	75	V
Peak reverse voltage	V _{RM}	100	V
Maximum average rectified current half wave rectification with resistive load at T _{amb} = 25°C and f ≥ 50Hz ⁽¹⁾	I _{F(AV)}	150	mA
Surge forward current at t < 1s and T _j = 25°C	I _{FSM}	500	mA
Maximum power dissipation at T _{amb} = 25°C ⁽¹⁾	P _{tot}	500	mW
Thermal resistance junction to ambient air ⁽¹⁾	R _{θJA}	350	°C/W
Maximum junction temperature	T _J	175	°C
Storage temperature range	T _S	-65 to +175	°C

Electrical Characteristics (T_A = 25°C unless otherwise noted)

Parameter	Symbol	Min.	Max.	Unit
Maximum forward voltage drop at I _F = 10mA	V _F	-	1.0	V
Leakage current at V _R = 50V at V _R = 75V	I _R	-	100 5	nA µA
Reverse breakdown voltage tested with 100µA pulses	V _{(BR)R}	100	-	V
Capacitance at V _F = V _R = 0V	C _{tot}	-	2	pF
Reverse recovery time from I _F = 10mA to I _R = 1mA, V _R = 6V, R _L = 100Ω	t _{rr}	-	4	ns
Rectification efficiency at f = 100MHz, V _{RF} = 2V	η _v	0.45	-	-

Note:

(1) Valid provided that leads at a distance of 8mm from case are kept at ambient temperature

Ratings and Characteristic Curves ($T_A = 25^\circ\text{C}$ unless otherwise noted)

